

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI HFT150-28 is Designed for

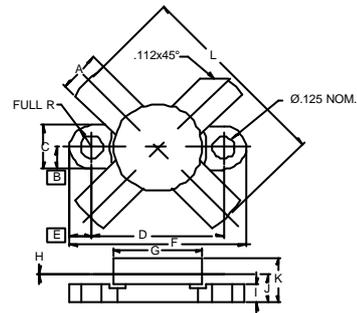
FEATURES:

- $P_G = 16$ dB min. at 150 W/30 MHz
- $IMD_3 = -28$ dBc max. at 150 W (PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|---------------|---------------------------------|
| I_D | 16 A |
| $V_{(BR)DSS}$ | 65 V |
| V_{GS} | ± 40 V |
| P_{DISS} | 300 W @ $T_C = 25^\circ C$ |
| T_J | $-65^\circ C$ to $+200^\circ C$ |
| T_{STG} | $-65^\circ C$ to $+150^\circ C$ |
| q_{JC} | $0.60^\circ C/W$ |

PACKAGE STYLE .500 4L FLG



| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .220 / 5.59 | .230 / 5.84 |
| B | .125 / 3.18 | |
| C | .245 / 6.22 | .255 / 6.48 |
| D | .720 / 18.28 | .730 / 18.54 |
| E | .125 / 3.18 | |
| F | .970 / 24.64 | .980 / 24.89 |
| G | .495 / 12.57 | .505 / 12.83 |
| H | .003 / 0.08 | .007 / 0.18 |
| I | .090 / 2.29 | .110 / 2.79 |
| J | .150 / 3.81 | .175 / 4.45 |
| K | .280 / 7.11 | |
| L | .980 / 24.89 | 1.050 / 26.67 |

ORDER CODE: ASI10616

CHARACTERISTICS $T_C = 25^\circ C$

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------------------------|--|---------|------------------|---------|--------------|
| $V_{(BR)DSS}$ | $V_{GS} = 0$ V $I_{DS} = 100$ mA | 65 | --- | --- | V |
| I_{DSS} | $V_{GS} = 0$ V $V_{DS} = 28$ V | --- | --- | 0.5 | mA |
| I_{GSS} | $V_{GS} = 20$ V $V_{DS} = 0$ V | --- | --- | 1.0 | mA |
| V_{GS} | $V_{DS} = 10$ V $I_D = 100$ mA | 1.0 | --- | 5.0 | V |
| V_{DS} | $V_{GS} = 10$ V $I_D = 10$ A | --- | --- | 1.5 | V |
| G_{FS} | $V_{DS} = 10$ V $I_D = 5$ A | 3.5 | --- | --- | mho |
| C_{ISS} C_{OSS} C_{RSS} | $V_{GS} = 28$ V $V_{DS} = 0$ V $F = 1.0$ MHz | --- | 375 188 26 | --- | pF |
| P_{IN} G_{PS} h | $V_{DD} = 28$ V $I_{DQ} = 250$ mA $P_{OUT} = 150$ W (PEP) $f = 175$ MHz | 50 | 10 | 15 | W dB % |